



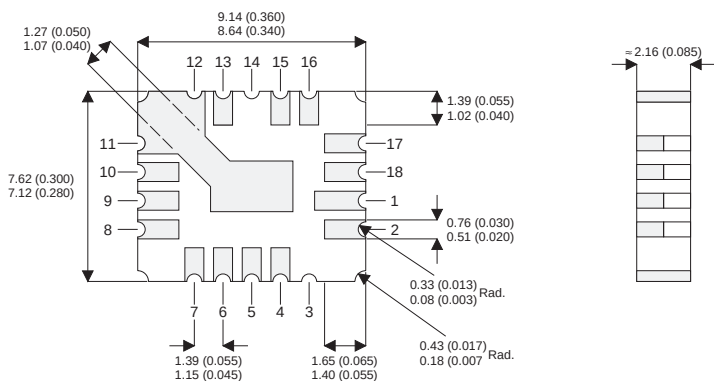
查询"2N6849U"供应商

SEMELAB

IRFE9130

MECHANICAL DATA

Dimensions in mm (inches)



LCC4

MOSFET	TRANSISTOR	PINS
GATE	BASE	4,5
DRAIN	COLLECTOR	1,2,15,16,17,18
SOURCE	EMITTER	6,7,8,9,10,11,12,13

P-CHANNEL POWER MOSFET

V_{DSS} -100V

$I_{D(cont)}$ -6.1A

$R_{DS(on)}$ 0.345 Ω

FEATURES

- SURFACE MOUNT
- SMALL FOOTPRINT
- HERMETICALLY SEALED
- DYNAMIC dv/dt RATING
- AVALANCHE ENERGY RATING
- SIMPLE DRIVE REQUIREMENTS
- LIGHT WEIGHT

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{GS}	Gate – Source Voltage	$\pm 20V$
I_D	Continuous Drain Current @ $T_{case} = 25^{\circ}C$	– 6.1A
I_D	Continuous Drain Current @ $T_{case} = 100^{\circ}C$	– 3.8A
I_{DM}	Pulsed Drain Current	– 24A
P_D	Power Dissipation @ $T_{case} = 25^{\circ}C$	22W
	Linear Derating Factor	0.17W/ $^{\circ}C$
E_{AS}	Single Pulse Avalanche Energy ²	92mJ
dv/dt	Peak Diode Recovery ³	– 5.5V/ns
T_J, T_{stg}	Operating and Storage Temperature Range	– 55 to +150 $^{\circ}C$
	Surface Temperature (for 5 sec).	300 $^{\circ}C$



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ELECTRICAL CHARACTERISTICS ($T_{\text{case}} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter		Test Conditions		Min.	Typ.	Max.	Unit
STATIC ELECTRICAL RATINGS							
BV _{DSS}	Drain – Source Breakdown Voltage	V _{GS} = 0	I _D = –1mA	–100			V
ΔBV _{DSS}	Temperature Coefficient of Breakdown Voltage	Reference to 25°C I _D = –1mA			– 0.10		V/°C
R _{DS(on)}	Static Drain – Source On–State Resistance ¹	V _{GS} = –10V	I _D = –3.8A			0.30	Ω
		V _{GS} = –10V	I _D = –6.1A			0.345	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS}	I _D = –250mA	– 2		– 4	V
g _{fs}	Forward Transconductance ¹	V _{DS} ≥ –15V	I _{DS} = –3.8A	2.5			S (V)
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} = 0	V _{DS} = 0.8BV _{DSS}			– 25	μA
			T _J = 125°C			– 250	
I _{GSS}	Forward Gate – Source Leakage	V _{GS} = –20V				– 100	nA
I _{GSS}	Reverse Gate – Source Leakage	V _{GS} = 20V				100	
DYNAMIC CHARACTERISTICS							
C _{iss}	Input Capacitance	V _{GS} = 0			800		pF
C _{oss}	Output Capacitance	V _{DS} = –25V			350		
C _{rss}	Reverse Transfer Capacitance	f = 1MHz			125		
Q _g	Total Gate Charge	V _{GS} = –10V		14.7		38.4	nC
Q _{gs}	Gate – Source Charge	I _D = –6.1A		1.0		7.1	
Q _{gd}	Gate – Drain (“Miller”) Charge	V _{DS} = 0.5BV _{DSS}		2.0		21	
t _{d(on)}	Turn–On Delay Time	V _{DD} = –50V I _D = –6.1A R _G = 7.5Ω				60	ns
t _r	Rise Time					140	
t _{d(off)}	Turn–Off Delay Time					140	
t _f	Fall Time					140	
SOURCE – DRAIN DIODE CHARACTERISTICS							
I _S	Continuous Source Current					–1.6	A
I _{SM}	Pulse Source Current ²					–24	
V _{SD}	Diode Forward Voltage ¹	I _S = –1.6A	T _J = 25°C			–4.7	V
		V _{GS} = 0					
t _{rr}	Reverse Recovery Time	I _F = –6.1A	T _J = 25°C			250	ns
Q _{rr}	Reverse Recovery Charge ¹	d _i / d _t ≤ –100A/μs V _{DD} ≤ –50V					3.0
t _{on}	Forward Turn–On Time			Negligible			
PACKAGE CHARACTERISTICS							
L _D	Internal Drain Inductance (measured from 6mm down drain lead to centre of die)				1.8		nH
L _S	Internal Source Inductance (from 6mm down source lead to source bond pad)				4.3		
THERMAL CHARACTERISTICS							
R _{θJC}	Thermal Resistance Junction – Case					5.8	°C/W
R _{θJPC}	Thermal Resistance Junction – PC Board					19	

Notes

- 1) Pulse Test: Pulse Width $\leq 300\text{ms}$, $\delta \leq 2\%$
- 2) Repetitive Rating – Pulse width limited by maximum junction temperature.